

Amendments to the Specification:

Please amend the specification as follows:

Page 1, after the Title, please insert the following paragraph:

This application is a National Stage application of PCT/JP2004/012239, filed August 19, 2004, which claims priority from Japanese patent application JP 2003-296439, filed August 20, 2003. The entire contents of each of the aforementioned applications are incorporated herein by reference.

Amend the paragraph on page 10, line 7, to page 11, line 2, as follows:

Referring to Fig. 5, there is shown a deposition source container for use in the vapor deposition apparatus according to this invention and, in this figure, there is shown a section of a deposition source container 50 for use in the vapor deposition apparatus of this invention. A material forming the illustrated deposition source container 50 is a material having low catalytic properties with respect to a deposition material to be filled and, specifically, **C** or an oxide or a nitride of an element selected from Si, Cr, Al, La, Y, ~~Ta, and Ti~~ **Ta, Ti and B** is chemically stable and suitable. For example, Al_2O_3 , Cr_2O_3 , AlN , Y_2O_3 , La_2O_3 , MgO , **BN, C,** or the like is preferable. Particularly, it is sufficient that the catalytic properties be low only at a portion to be in contact with the deposition material and, therefore, the foregoing material with the low catalytic properties may be formed on the inner surface of a deposition source container made of a high thermal conductivity material, such as tungsten, having a thermal conductivity of 1 W/mK or more. The formation may be carried out according to a plasma spraying method or by sputtering, for example, Al according to a sputtering method and then oxidizing or nitriding it. When the deposition source container is made of the high thermal conductivity material, the heat from a heater provided outside the container can be efficiently conducted to the deposition material and, therefore, it is suitable in terms of maintaining homogeneity of a deposited film and enhancing the energy efficiency. The structure of the deposition source container for use in the vapor deposition apparatus of this invention is not

limited to the foregoing bottomed hollow cylindrical shape and may have any shape as long as the deposition material can be loaded and heated. As such a shape, a boat shape or a dish shape can be cited as an example.

Amend the paragraph on page 12, lines 18-23, as follows:

A turbomolecular pump was used as the primary pump 12, while a screw dry pump was used as the secondary pump 13. In this case, 100 sccm Ar as an inert gas was led through the gas introduction mechanism 17 to thereby suppress back or reverse diffusion of impurities from the screw dry pump 13. A Cu gasket was used as the secondary gasket 16, while a perfluoroelastomer gasket was used as the first gasket 15.